

BZX84J series

Single Zener diodes

Rev. 2 — 1 August 2011 Product data sheet

1. Product profile

1.1 General description

General-purpose Zener diodes in a SOD323F (SC-90) very small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Non-repetitive peak reverse power dissipation: ≤ 40 W
- Total power dissipation: ≤ 550 mW
- AEC-Q101 qualified
- Small plastic package suitable for surface-mounted design
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Two tolerance series: ±2 % and ±5 %
- Low differential resistance

1.3 Applications

- General regulation functions

1.4 Quick reference data

Table 1. Quick reference data

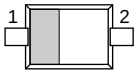
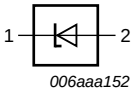
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_F	forward voltage	I_F = 100 mA	[1]	-	-	1.1	V
P_{ZSM}	non-repetitive peak reverse power dissipation		[2]	-	-	40	W

[1] Pulse test: $t_p \leq 300\ \mu s$; $\delta \leq 0.02$.

[2] t_p = 100 μs; square wave; T_j = 25 °C prior to surge

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Symbol
1	cathode	[1]		
2	anode			

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BZX84J-B2V4 to BZX84J-C75[1]	SC-90	plastic surface-mounted package; 2 leads	SOD323F

[1] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

4. Marking

Table 4. Marking codes

Type number	Marking code	Type number	Marking code	Type number	Marking code	Type number	Marking code
BZX84J-B2V4	SL	BZX84J-B15	SC	BZX84J-C2V4	U3	BZX84J-C15	TV
BZX84J-B2V7	SM	BZX84J-B16	SD	BZX84J-C2V7	U4	BZX84J-C16	TW
BZX84J-B3V0	ST	BZX84J-B18	SE	BZX84J-C3V0	U9	BZX84J-C18	TX
BZX84J-B3V3	SU	BZX84J-B20	SF	BZX84J-C3V3	UA	BZX84J-C20	TY
BZX84J-B3V6	SV	BZX84J-B22	SG	BZX84J-C3V6	UB	BZX84J-C22	TZ
BZX84J-B3V9	SW	BZX84J-B24	SH	BZX84J-C3V9	UC	BZX84J-C24	U1
BZX84J-B4V3	SZ	BZX84J-B27	SK	BZX84J-C4V3	UF	BZX84J-C27	U2
BZX84J-B4V7	TA	BZX84J-B30	SN	BZX84J-C4V7	UG	BZX84J-C30	U5
BZX84J-B5V1	TD	BZX84J-B33	SP	BZX84J-C5V1	UL	BZX84J-C33	U6
BZX84J-B5V6	TE	BZX84J-B36	SR	BZX84J-C5V6	UM	BZX84J-C36	U7
BZX84J-B6V2	TH	BZX84J-B39	SS	BZX84J-C6V2	UR	BZX84J-C39	U8
BZX84J-B6V8	TK	BZX84J-B43	SX	BZX84J-C6V8	US	BZX84J-C43	UD
BZX84J-B7V5	TM	BZX84J-B47	SY	BZX84J-C7V5	UU	BZX84J-C47	UE
BZX84J-B8V2	TN	BZX84J-B51	TB	BZX84J-C8V2	UV	BZX84J-C51	UH
BZX84J-B9V1	TP	BZX84J-B56	TC	BZX84J-C9V1	UW	BZX84J-C56	UK
BZX84J-B10	S8	BZX84J-B62	TF	BZX84J-C10	TR	BZX84J-C62	UN
BZX84J-B11	S9	BZX84J-B68	TG	BZX84J-C11	TS	BZX84J-C68	UP
BZX84J-B12	SA	BZX84J-B75	TL	BZX84J-C12	TT	BZX84J-C75	UT
BZX84J-B13	SB	-	-	BZX84J-C13	TU	-	-

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
I_F	forward current			-	250	mA
I_{ZSM}	non-repetitive peak reverse current		[1]	-	see Table 8 and 9	
P_{ZSM}	non-repetitive peak reverse power dissipation		[1]	-	40	W
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[2]	-	550	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			−55	+150	°C
T_{stg}	storage temperature			−65	+150	°C

[1] $t_p = 100$ µs; square wave; $T_j = 25$ °C prior to surge

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	230	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[2]	-	-	55	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2.

[2] Soldering point of cathode tab.

7. Characteristics

Table 7. Characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_F	forward voltage		[1]				
		I_F = 10 mA		-	-	0.9	V
		I_F = 100 mA		-	-	1.1	V

[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.

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